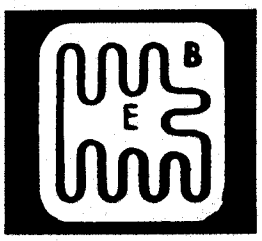
CHIP NUMBER

200



Base: .006" x .006" (0.15mm x 0.15mm)
Emitter: .005" x .006" (0.13mm x 0.15mm)

PNP EPITAXIAL PLANAR POWER TRANSISTOR**

CONTACT METALLIZATION

Base and emitter: > 30,000 Å Aluminum

Collector: Gold
(Polished silicon or "Chrome Nickel Silver" also available)

Also available on:

MOLY PEDESTAL
Size: .140" Diameter (3.56mm)
Thickness: .010" (0.25mm)

BeO PEDESTAL
Size: .142" x .178" (3.61mm x 4.52mm)
Thickness: .028" (0.71mm)

ASSEMBLY RECOMMENDATIONS

It is advisable that:
a) the chip be eutectically mounted with gold silicon preform 98/2%.
b) 2 mil (0.051mm) aluminum wire be ultrasonically attached to the base and emitter contacts.

TYPICAL ELECTRICAL CHARACTERISTICS AT 25°C

The following typical electrical characteristics apply for a completely finished component employing the chip number 200 in a TO-5 or equivalent case:

V_{CEO}	$V_{CE(s)}$ @	I_C	I_B	h_{FE} @	I_C	V_{CE}
>200V	<0.4V	50mA	5mA	>30	50mA	10V
>250V	<0.4V	50mA	5mA	>30	50mA	10V
>300V	<0.4V	50mA	5mA	>30	50mA	10V
>350V	<0.4V	50mA	5mA	>30	50mA	10V

V_{CEO}	V_{CEX}	V_{EBO}	f_T	C_{OBO}	θ_{JC}
>200V	210V	>5V	15MHz	<10pF	<15°C/W
>250V	260V	>5V	15MHz	<10pF	<15°C/W
>300V	300V	>5V	15MHz	<10pF	<15°C/W
>350V	350V	>5V	15MHz	<10pF	<15°C/W

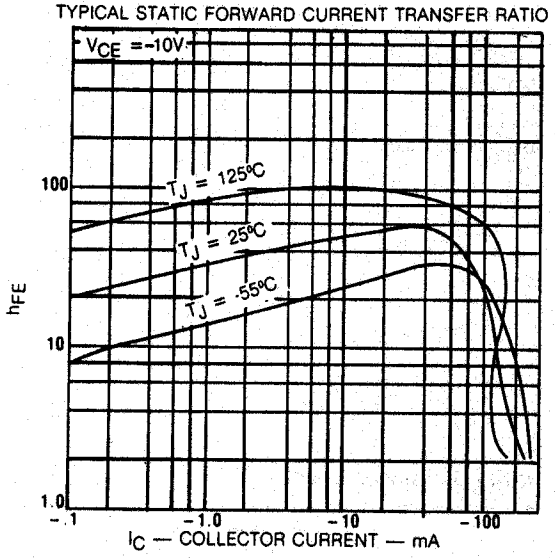
Typical Device Types: JAN2N5415, JAN2N5416, SDT1A10

h_{FE} ranges available at I_C = 50mA, V_{CE} = 5V, 20-80, 30-120

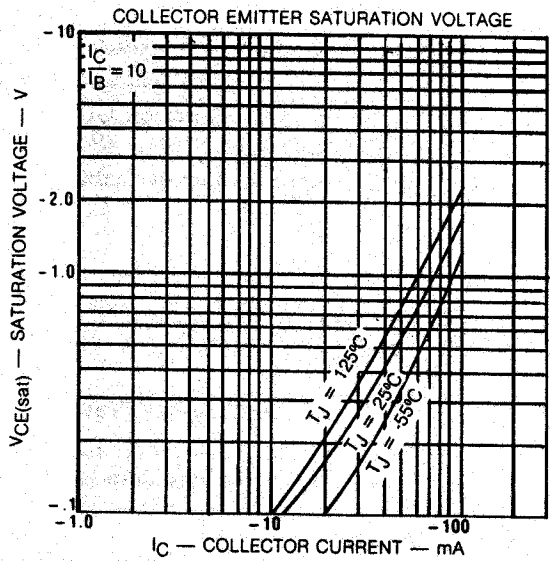
**The respective NPN complement is chip number 100.

CHIP TYPE 200

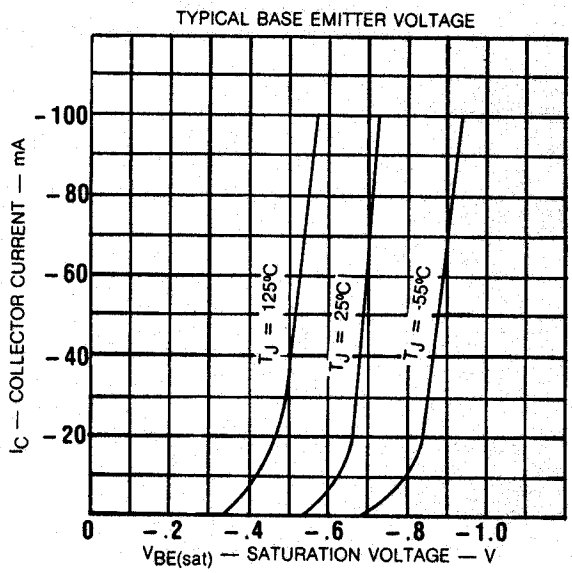
TYPICAL STATIC FORWARD CURRENT TRANSFER RATIO



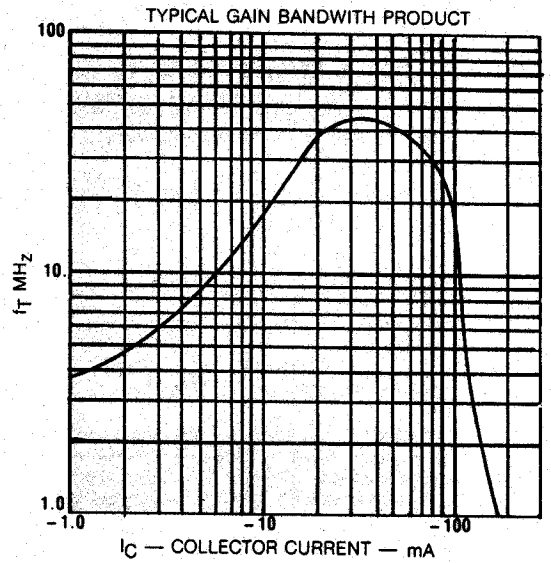
COLLECTOR EMITTER SATURATION VOLTAGE



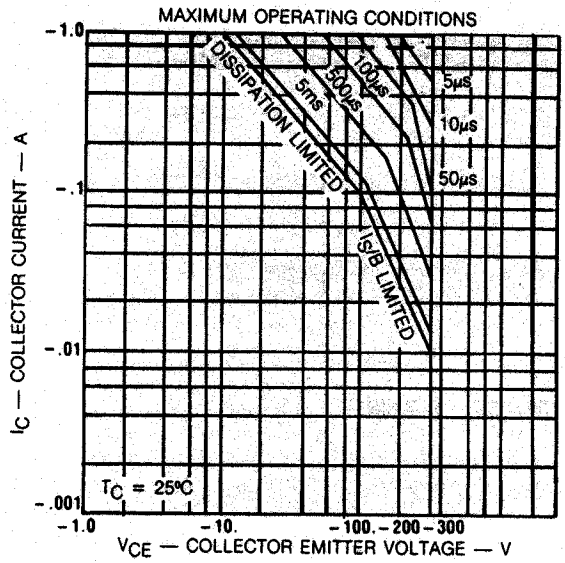
TYPICAL BASE EMITTER VOLTAGE



TYPICAL GAIN BANDWITH PRODUCT



MAXIMUM OPERATING CONDITIONS



NOTE:
PERFORMANCE CURVES REPRESENT LOW TO MIDDLE CEO VOLTAGE RANGE OF THIS PRODUCT